

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -20V	Steady State	T _A = +25°C T _A = +70°C	I _D	-9.9 -7.9	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-12.5 -10.0	A
Continuous Drain Current (Note 6) V _{GS} = -6V	Steady State	T _A = +25°C T _A = +70°C	I _D	-8.2 -6.5	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	-11.0 -8.7	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-3.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-80	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	1.45	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	88	°C/W
	t < 10s		50	°C/W
Total Power Dissipation (Note 6)		P _D	1.82	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	70	°C/W
	t < 10s		41	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	7.6	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-50 to +155	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.7	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	9	11	mΩ	V _{GS} = -20V, I _D = -12A
		—	10	13		V _{GS} = -10V, I _D = -10A
		—	12.7	17		V _{GS} = -6V, I _D = -10A
Forward Transfer Admittance	Y _{fs}	—	21	—	S	V _{DS} = -5V, I _D = -10A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2246	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	352	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	294	—	pF	
Gate Resistance	R _g	—	5.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	20.5	—	nC	V _{GS} = -10V, V _{DS} = -15V, I _D = -12A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	41	—	nC	
Gate-Source Charge	Q _{gs}	—	7.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	8.0	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	11.3	—	ns	V _{DD} = -15V, V _{GS} = -10V, R _L = 1.25Ω, R _G = 3Ω
Turn-On Rise Time	t _R	—	15.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	38.0	—	ns	
Turn-Off Fall Time	t _F	—	22.0	—	ns	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

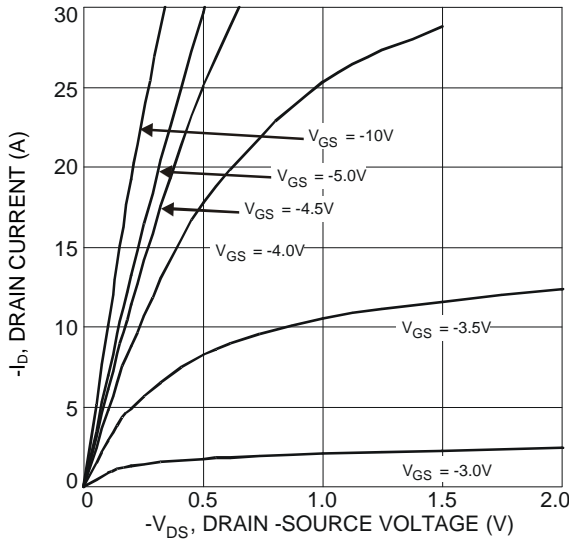


Fig. 1 Typical Output Characteristics

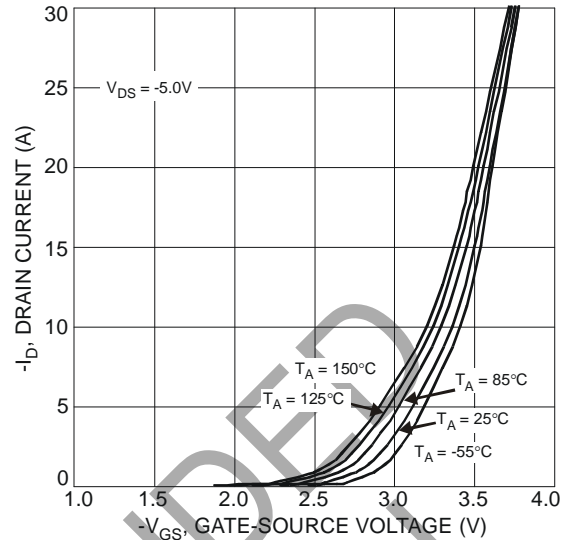


Fig. 2 Typical Transfer Characteristics

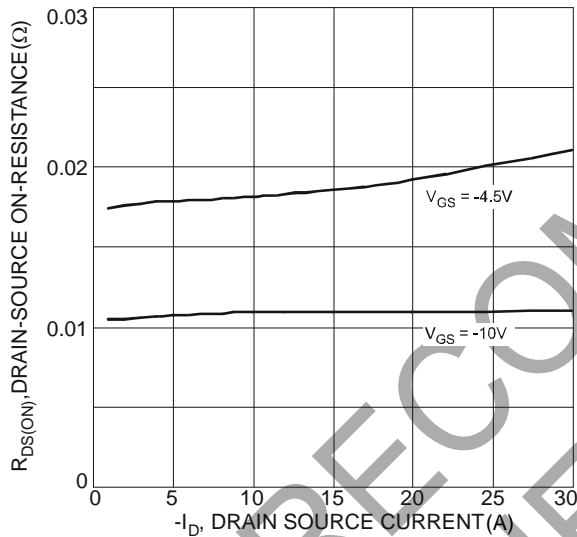


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

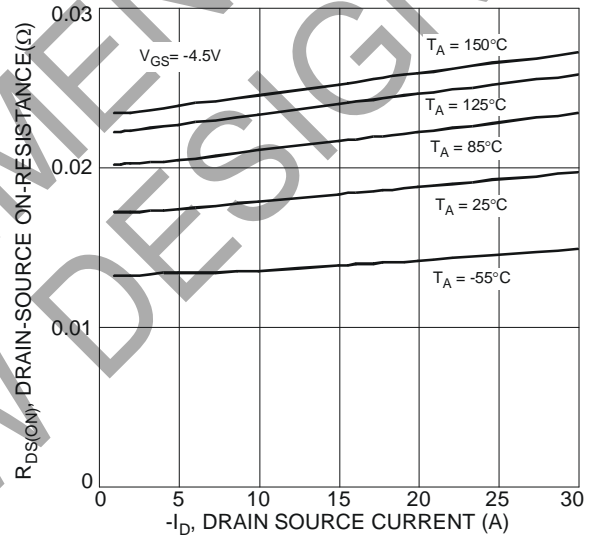


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

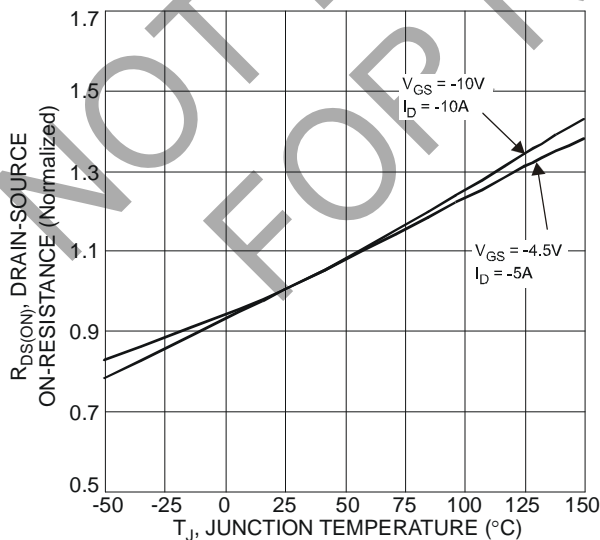


Fig. 5 On-Resistance Variation with Temperature

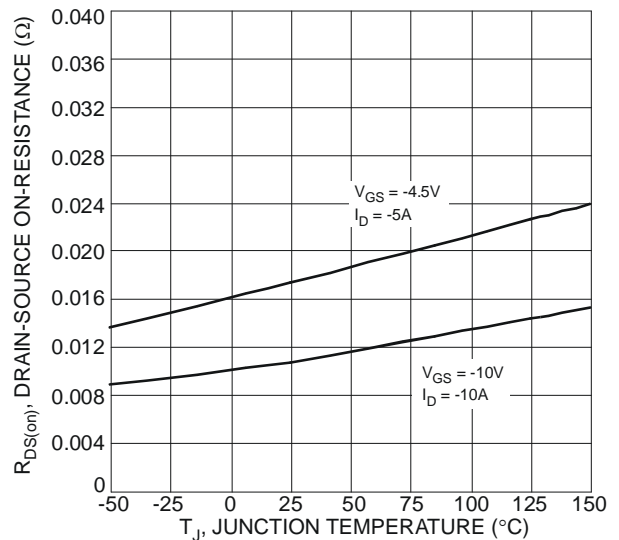


Fig. 6 On-Resistance Variation with Temperature

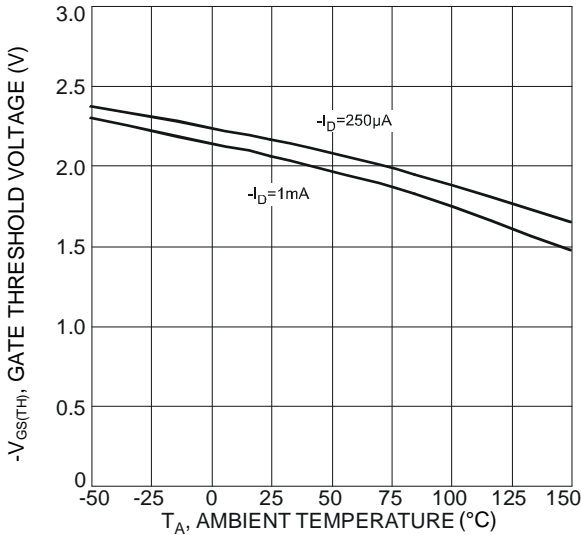


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

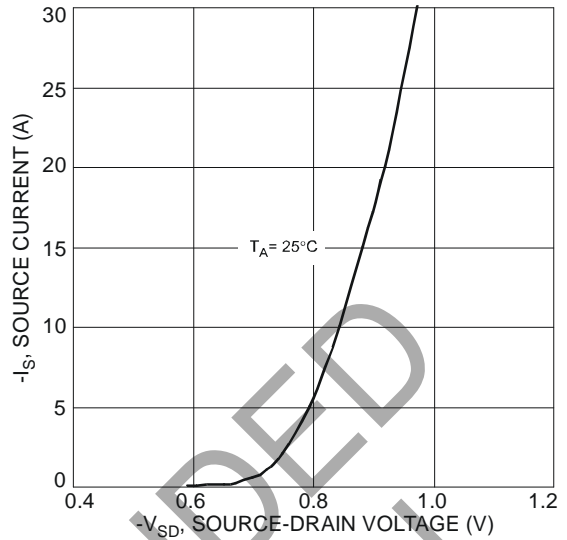


Fig. 8 Diode Forward Voltage vs. Current

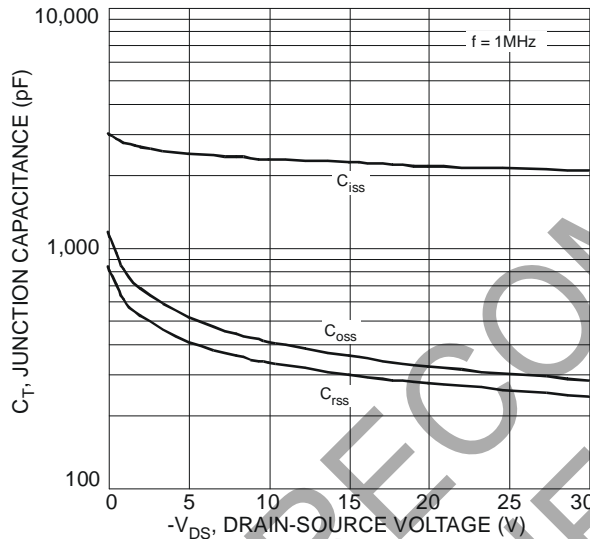


Fig. 9 Typical Junction Capacitance

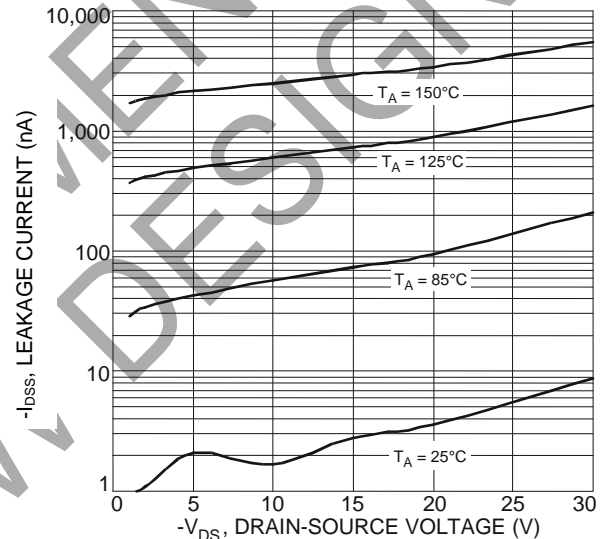


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

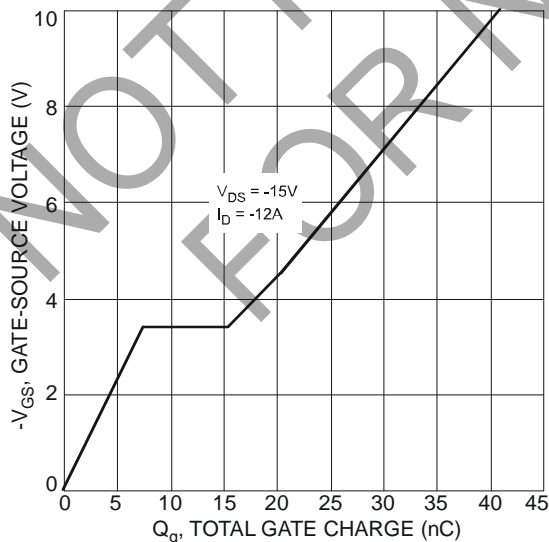


Fig. 11 Gate-Charge Characteristics

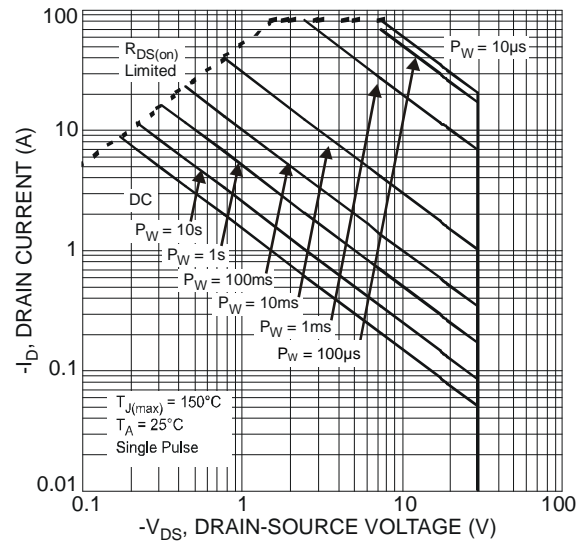
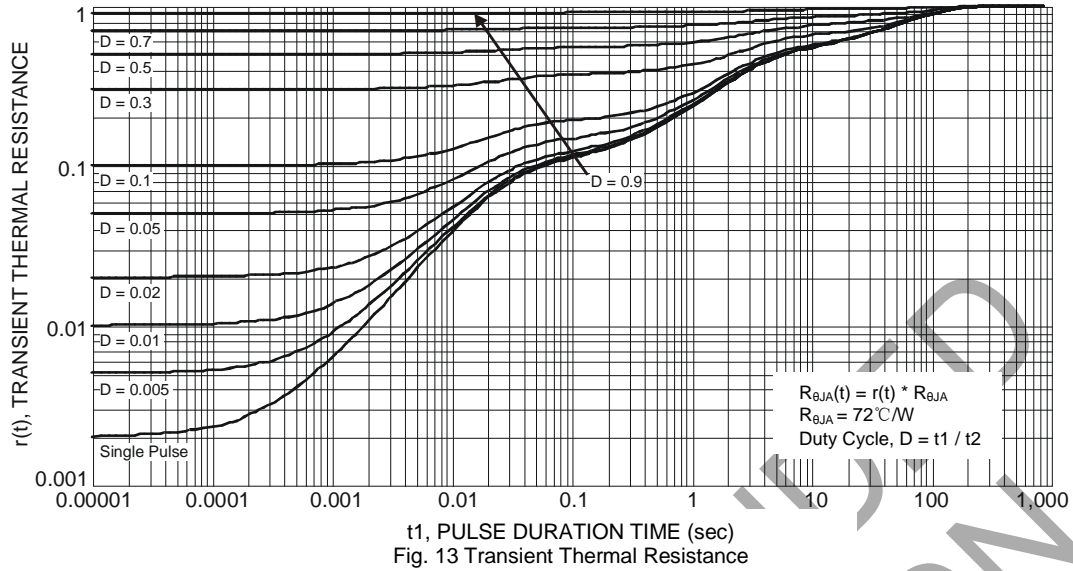


Fig. 12 SOA, Safe Operation Area

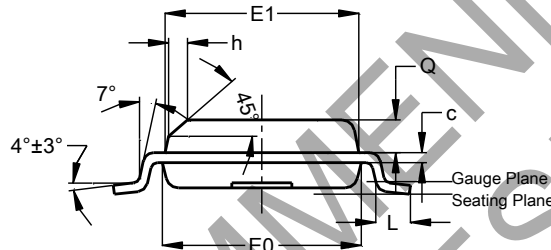
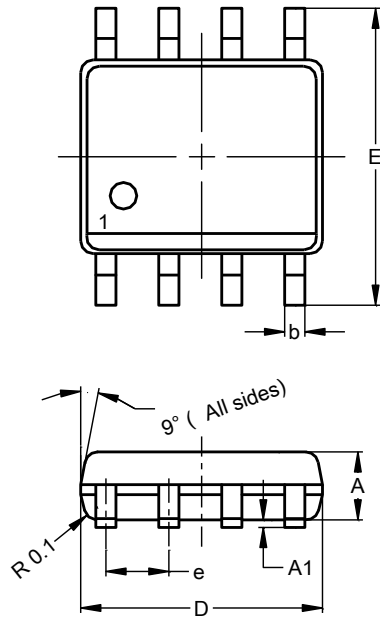


NOT RECOMMENDED FOR NEW DESIGN

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

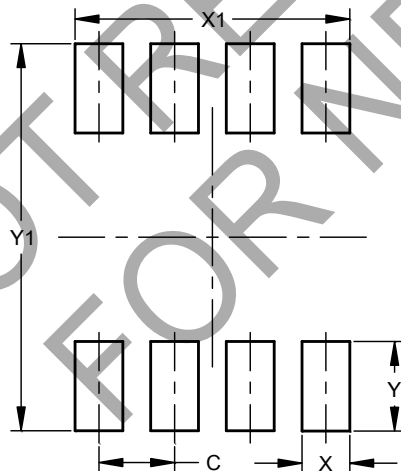


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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